

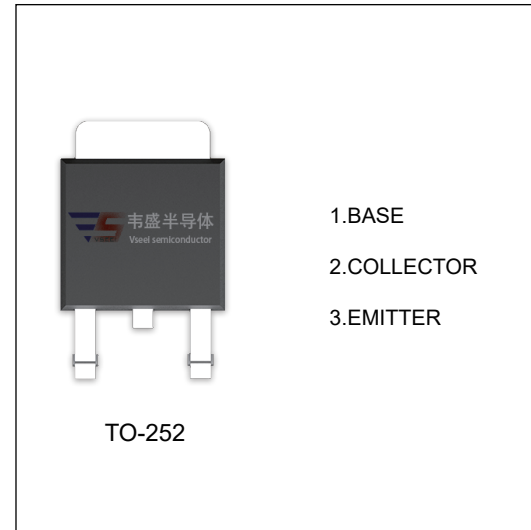
2SB1184 TRANSISTOR (PNP)

FEATURES

- Low $V_{CE(sat)}$ $V_{CE(sat)} = -0.5V$ (Typ.) ($I_C/I_B = -2A / -0.2A$)
- Complements the 2SD1760 / 2SD1864.

MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-3	A
P_C	Collector Power Dissipation	1	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50mA, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -3V, I_C = -0.5A$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1.5A, I_B = -0.15A$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -0.5A, f = 30MHz$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		50		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking			

Static Characteristic
